

IN THE CLAIMS

The following is a listing of the claims in accordance with 37 C.F.R. §1.121.

1. (currently amended) A sensor device comprising:
a multiplicity of sensor elements arranged at a front surface of a substrate, each of said sensor elements being in contact with material of said substrate; and
a multiplicity of barriers arranged in said material of said substrate to reduce the coupling of a form of energy between any of said sensor elements, each barrier posing an obstacle to the propagation of said form of energy impinging thereon, wherein the multiplicity of barriers extend into said material of said substrate but not completely through said material of said substrate, and wherein said barriers and adjoining portions of said substrate are coated with a thin layer of insulating material.
2. (original) The device as recited in claim 1, wherein said barriers are located in areas between neighboring sensor elements.
3. (original) The device as recited in claim 1, wherein said sensor elements are arranged in a row with spacing between neighboring sensor elements, and said barriers are interleaved with said sensor elements, each pair of neighboring sensor elements having a respective barrier therebetween.
4. (original) The device as recited in claim 1, wherein said sensor elements are arranged in a two-dimensional array with spacing between neighboring sensor elements, and said barriers form an interconnected network that defines a multiplicity of bounded areas, each bounded area being occupied by a respective sensor element.

5. (currently amended) The device as recited in claim 1, wherein each of said sensor elements comprises a respective multiplicity of ultrasonic transducer ~~ULTRASONIC TRANSDUCER~~ cells electrically connected together.

6. (original) The device as recited in claim 1, wherein each of said barriers comprises a respective trench.

7. (original) The device as recited in claim 6, wherein each of said trenches starts at said front surface of said substrate and has a depth less than a thickness of said substrate.

8. (original) The device as recited in claim 6, wherein each of said trenches starts at a rear surface of said substrate and has a depth less than a thickness of said substrate.

9. (original) The device as recited in claim 6, wherein each of said sensor elements comprises a respective ultrasonic transducer element, and said trenches are filled with acoustically attenuative material.

10. (original) The device as recited in claim 6, wherein each of said sensor elements comprises a respective ultrasonic transducer element, further comprising a body of acoustically attenuative material that supports said substrate.

11. (canceled).

12. (original) The device as recited in claim 6, wherein a surface of each of said trenches is coated with an electrically conductive material that is grounded to electrically isolate one sensor element from the next.

13. (withdrawn) The device as recited in claim 1, wherein each of said barriers comprises a respective volume of said material of said substrate that has doping agents implanted therein, said doped material having the ability to substantially prevent the flow of electric current therethrough.

14. (withdrawn) The device as recited in claim 13, wherein each of said implanted volumes comprises a conductive region that is grounded to prevent charge transfer from one element to the next.

15. (withdrawn) The device as recited in claim 13, wherein each of said implanted volumes comprises a respective semiconductive junction.

16. (withdrawn) The device as recited in claim 13, wherein each of said volumes comprises a respective pair of back-to-back pn junction diodes.

17. (withdrawn) The device as recited in claim 13, wherein each of said implanted volumes comprises a respective near-insulating region.

18.-34. (canceled).

35. (currently amended) An ultrasonic transducer device comprising:
a multiplicity of ultrasonic transducer elements arranged at a front surface of a substrate, each of said transducer elements comprising a respective group of ultrasonic transducer cells electrically connected together and acoustically coupled to said substrate;
and

a multiplicity of trenches in said material of said substrate, said trenches being disposed in areas between said transducer elements, and said trenches obstructing the propagation of acoustic wave energy therethrough, wherein the multiplicity of trenches extend into said material of said substrate but not completely through said material of said

substrate, and wherein said trenches and adjoining portions of said substrate are coated with a thin layer of insulating material.

36. (original) The device as recited in claim 35, wherein said trenches are filled with acoustically attenuative material.

37. (original) The device as recited in claim 35, further comprising a body of acoustically attenuative material acoustically coupled to a rear face of said substrate.

38. (canceled).

39. (original) The device as recited in claim 35, wherein a surface of each of said trenches is coated with an electrically conductive material that is grounded to electrically isolate one transducer element from the next.

40. (withdrawn) A sensor device comprising:
a multiplicity of sensor elements arranged at a front surface of a substrate, each of said sensor elements being in contact with material of said substrate; and
a multiplicity of zones of dopant implantation in said material of said substrate, said zones being disposed in areas between said sensor elements, and said zones obstructing the flow of electric current therethrough.

41. (withdrawn) The device as recited in claim 40, wherein each of said zones is doped to transfer charge to ground, preventing the flow of electric current from one sensor element to the next.

42. (withdrawn) The device as recited in claim 40, wherein each of said zones comprises a respective semiconductive junction.

43. (withdrawn) The device as recited in claim 40, wherein each of said zones comprises a respective pair of back-to-back pn junction diodes.

44. (withdrawn) The device as recited in claim 40, wherein each of said zones comprises a respective near-insulating region.

45.-50. (canceled).